

MMH40.12

Single-phase half-control

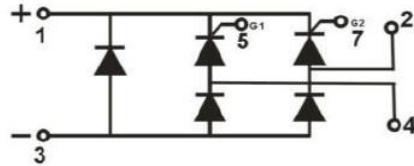
Features:

- International standard package
- Isolation voltage 3000V ~
- Simple mounting
- UL recognized, file no. E312789



Typical applications:

- Various rectifier power
- AC/DC motor control
- Heater control
- Light dimmer
- Frequency converters



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1300	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1200	V
$I_T, I_{F(AV)}$	On-state/forward average current	Single-phase full wave rectifying circuit, $T_c = 85^\circ\text{C}$			40	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^\circ\text{C}$			10	mA
I_{TSM}, I_{FSM}	Surge non repetitive current	10ms half sine wave $T_j = 45^\circ\text{C}$			400	A
$I^2 t$	$I^2 t$ for fusing coordination	Thyristor: $V_R = 60\% V_{RRM}$ $T_j = 45^\circ\text{C}$			800	A^2s
V_{TO}	Threshold voltage	$T_j = 125^\circ\text{C}$			0.90	V
r_T	On-state slope resistance	$T_j = 125^\circ\text{C}$			12	$\text{m}\Omega$
V_{TM}, V_{FM}	Thyristor: Peak on-state voltage	$T = 25^\circ\text{C}; I_T = 60\text{A}$			1.60	V
	Diode: Peak forward voltage	$T = 25^\circ\text{C}; I_F = 60\text{A}$			1.40	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}, T_j = 125^\circ\text{C}$, linear voltage rise			500	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of off-state current	$T_j = 25^\circ\text{C}$, Gate source 1,5A, $T_r < 0,5\mu\text{s}$			150	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current	$V_A = 12\text{V}, I_A = 1\text{A}, T_j = 25^\circ\text{C}$	20		150	mA
V_{GT}	Gate trigger voltage		0.70		1.80	V
I_{GD}	Gate non-trigger current	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$			10	mA
V_{GD}	Gate non-trigger voltage				0.25	V
P_{GM}	Gate peak power				10	W
$P_{G(AV)}$	Gate average power				0.5	W
I_H	Holding current	$T_j = 25^\circ\text{C}$	20		150	mA
I_L	Latching current	$T_j = 25^\circ\text{C}$	100		400	mA
$R_{th(j-c)}$	Thermal resistance junction to case	per module			0.39	$^\circ\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal resistance case to sink	per module			0.10	$^\circ\text{C}/\text{W}$
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$		3000		V
F_M	Mounting torque - copper plate (M5)		2.5		3.5	N·m
T_{stg}	Storage Temperature		-40		125	$^\circ\text{C}$
T_j	Operating Temperature		-40		125	$^\circ\text{C}$
W_t	Weight			70		g
Outline	M14					

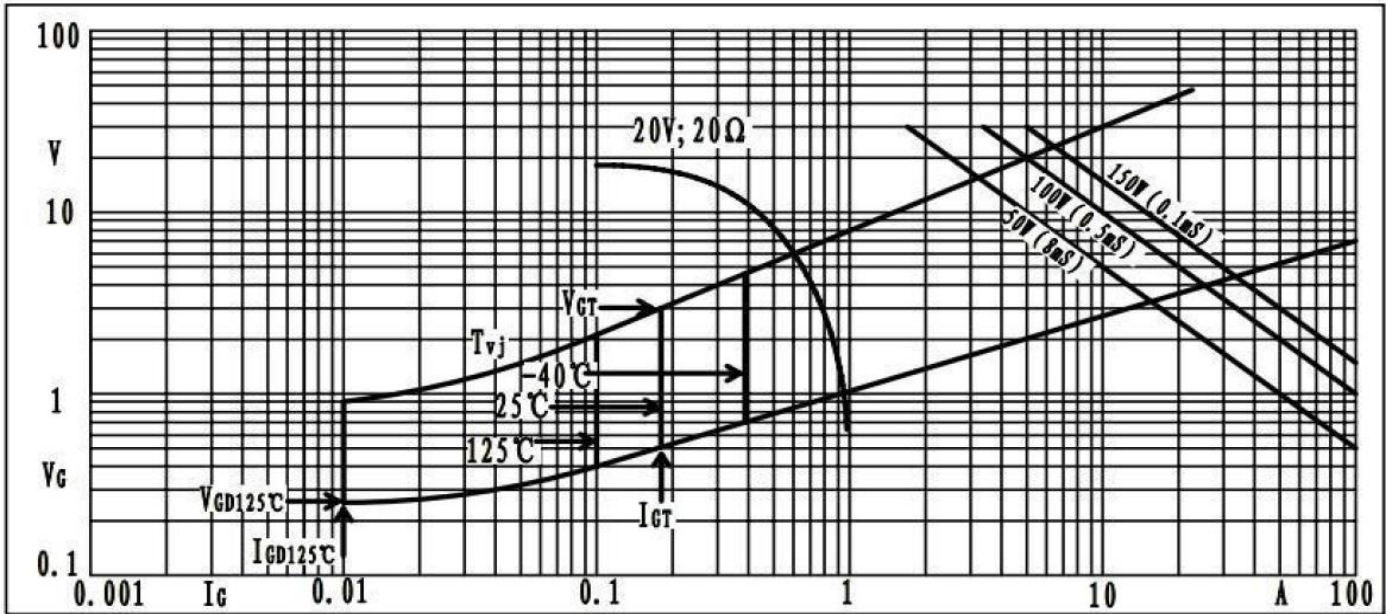


Fig1. Gate trigger characteristics

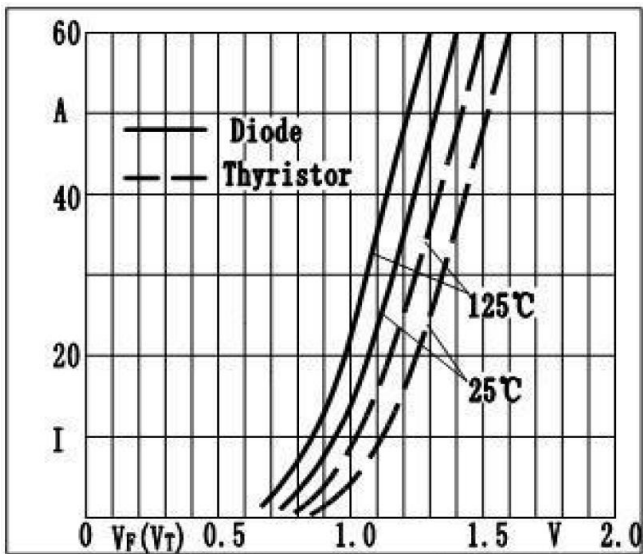


Fig2. Forward characteristics

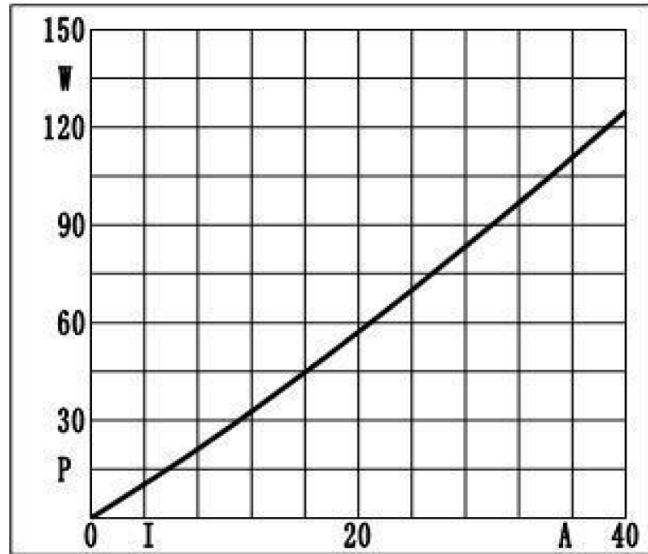


Fig3. Power dissipation

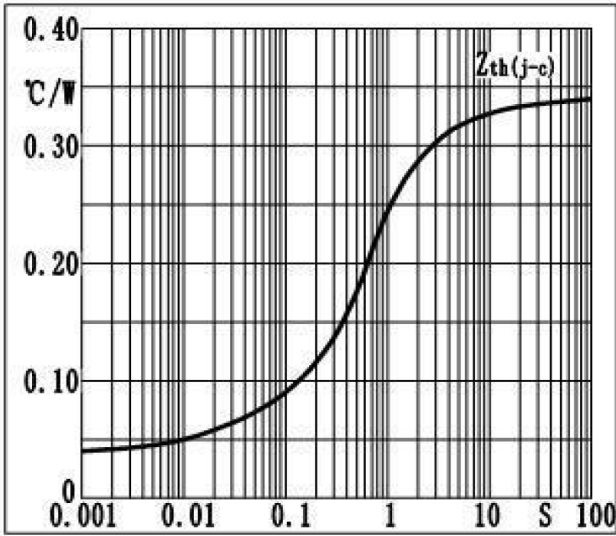


Fig4. Transient thermal impedance

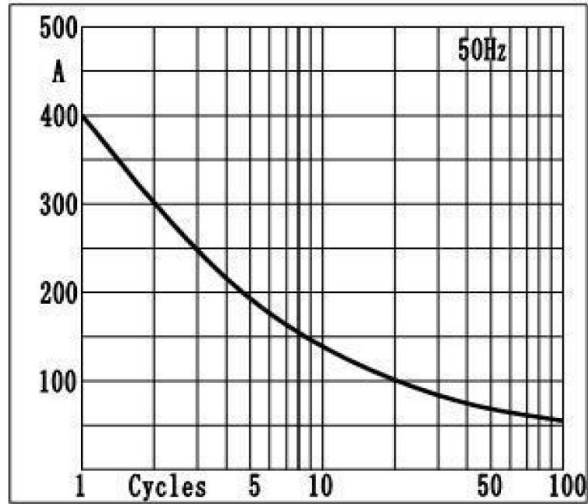


Fig5. Max non-repetitive forward surge current

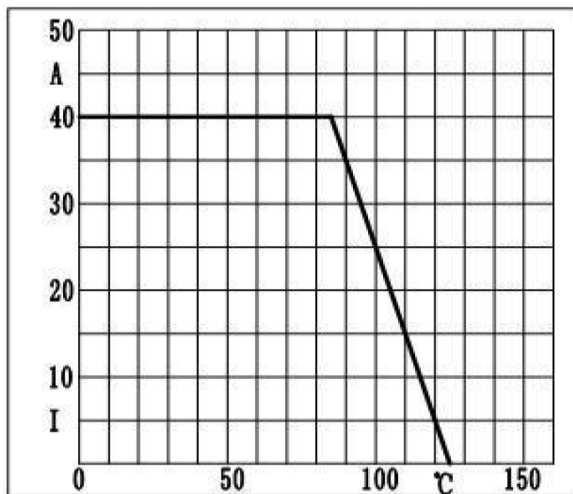
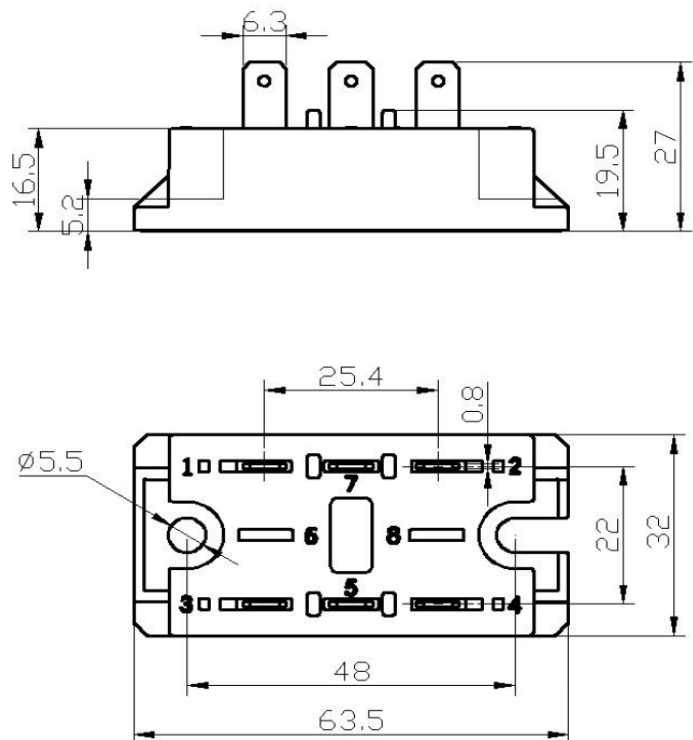


Fig6. Forward current derating curve



S.CO.M.E.S. Srl

Via Enrico Mattei, 6/8 - 26283 - Castiglione d'Adda (LO) - Italy

Phone: +39 0377 901243 Fax: +39 0377 900206